

Performance of FPCCD vertex detector

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ACFA 9, IHEP ,Beijin

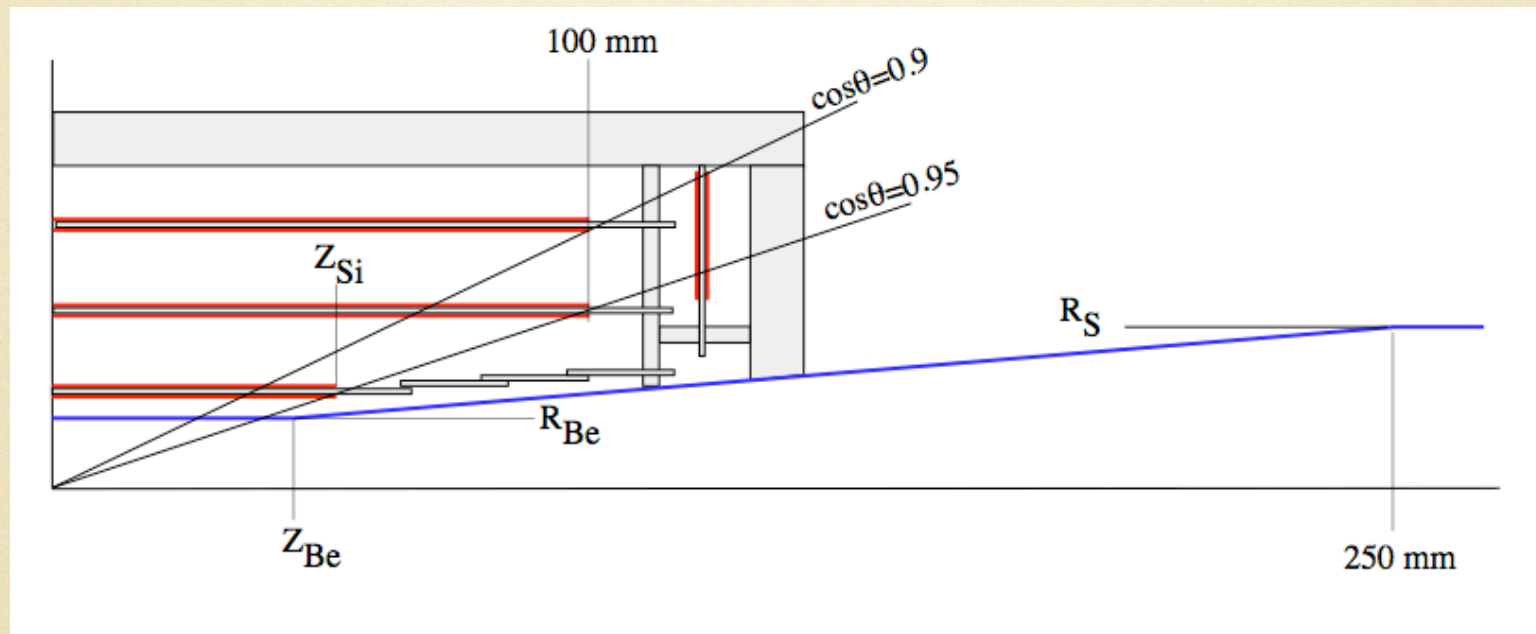
Outline

- FPCCD and Vertex Detector Structure
- Impact Parameter Resolution
- Pair Background in Vertex Detector
- Track finding / fitting in Vertex Detector
- Cluster Shape Analysis
- Energy Loss in Thin Material

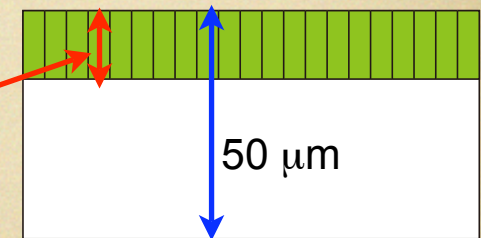
FPCCD features

- Large area device fabrication can be made
 - > small dead area between sensors on ladders
- Fully depleted -> Less smearing
- Very small pixel size
 - > good hit position resolution ($\sim 2 \mu\text{m}$)
 - > Less occupancy
- No charge transfer during a bunch train
 - > Avoid EM noise from beam
- Very thin (a few $10 \mu\text{m}$)
 - > Less Multiple scattering, but small signals
- High back ground hit rate accumulated ($\sim 40 \text{ hits} / \text{mm}^2 / \text{train}$)
 - > Need good background rejection and tracking method

Structure of Vertex Detector

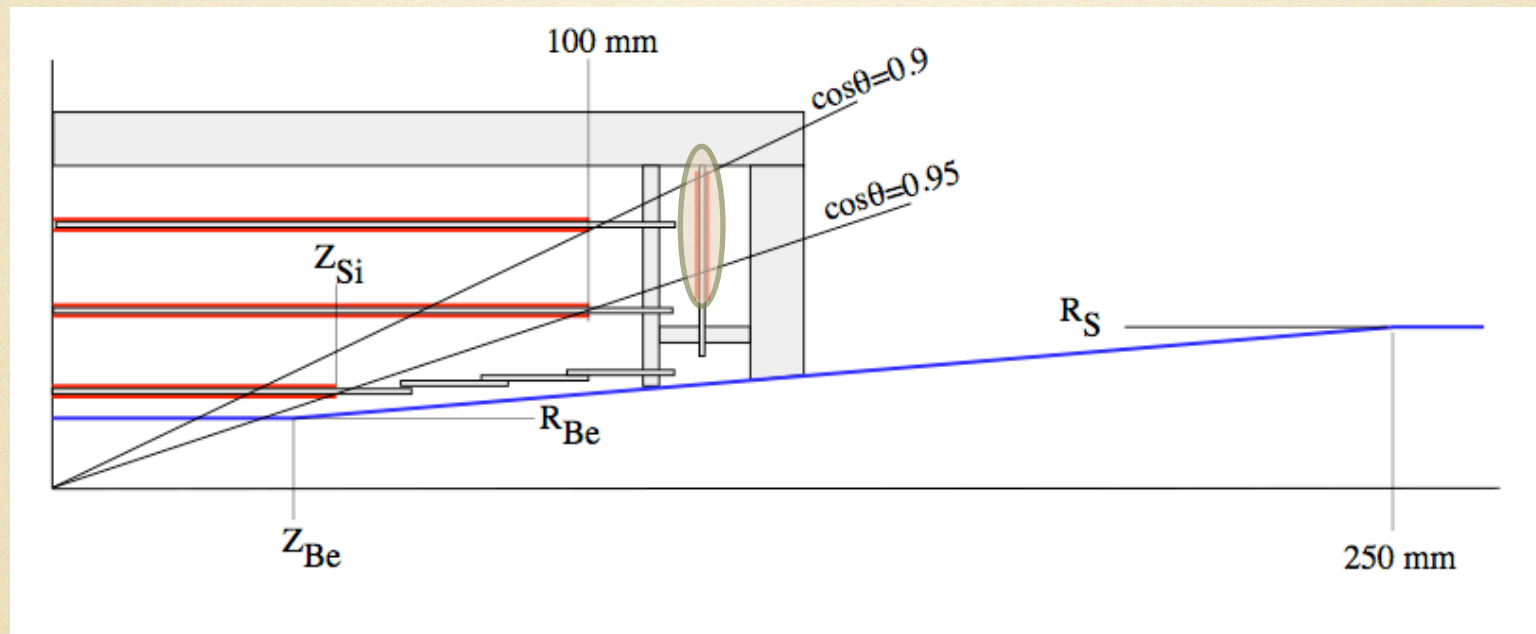


- 3 doublets structure
- Silicon thickness : $50 \mu\text{m}$ ($0.53 \times 10^{-3} X_0$)
- Depletion layer thickness : $15 \mu\text{m}$
- Pixel size : $5 \times 5 \mu\text{m}$

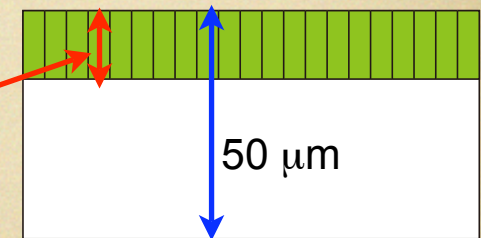


CCD Cross Section

Structure of Vertex Detector

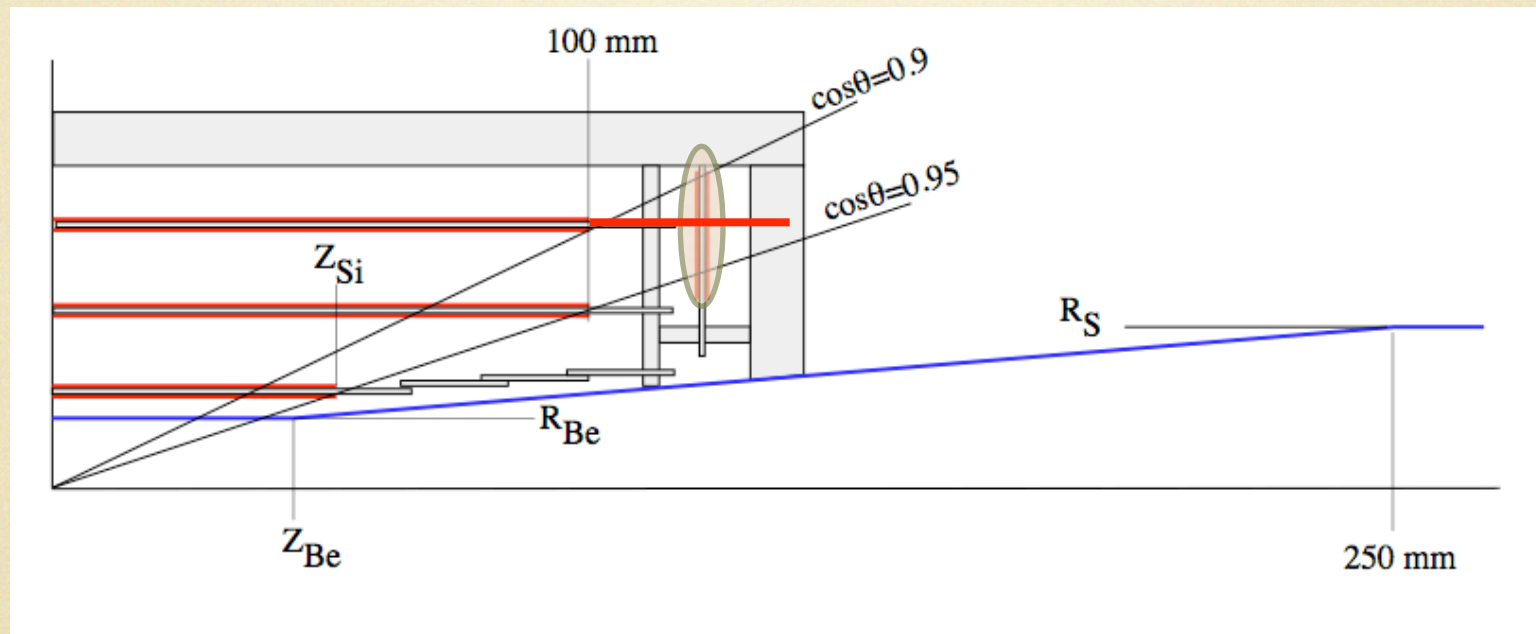


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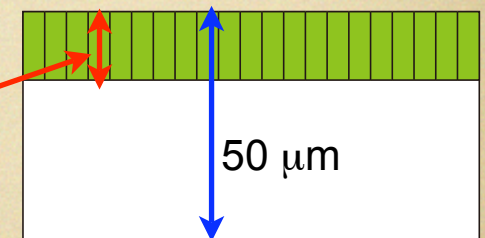


CCD Cross Section

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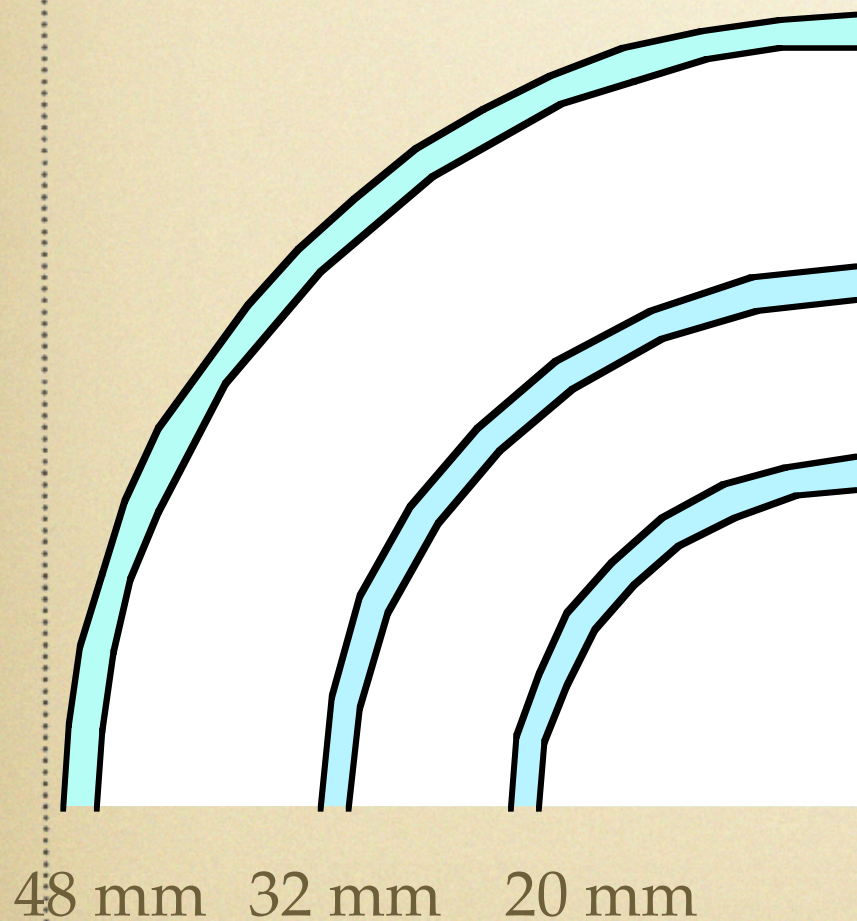


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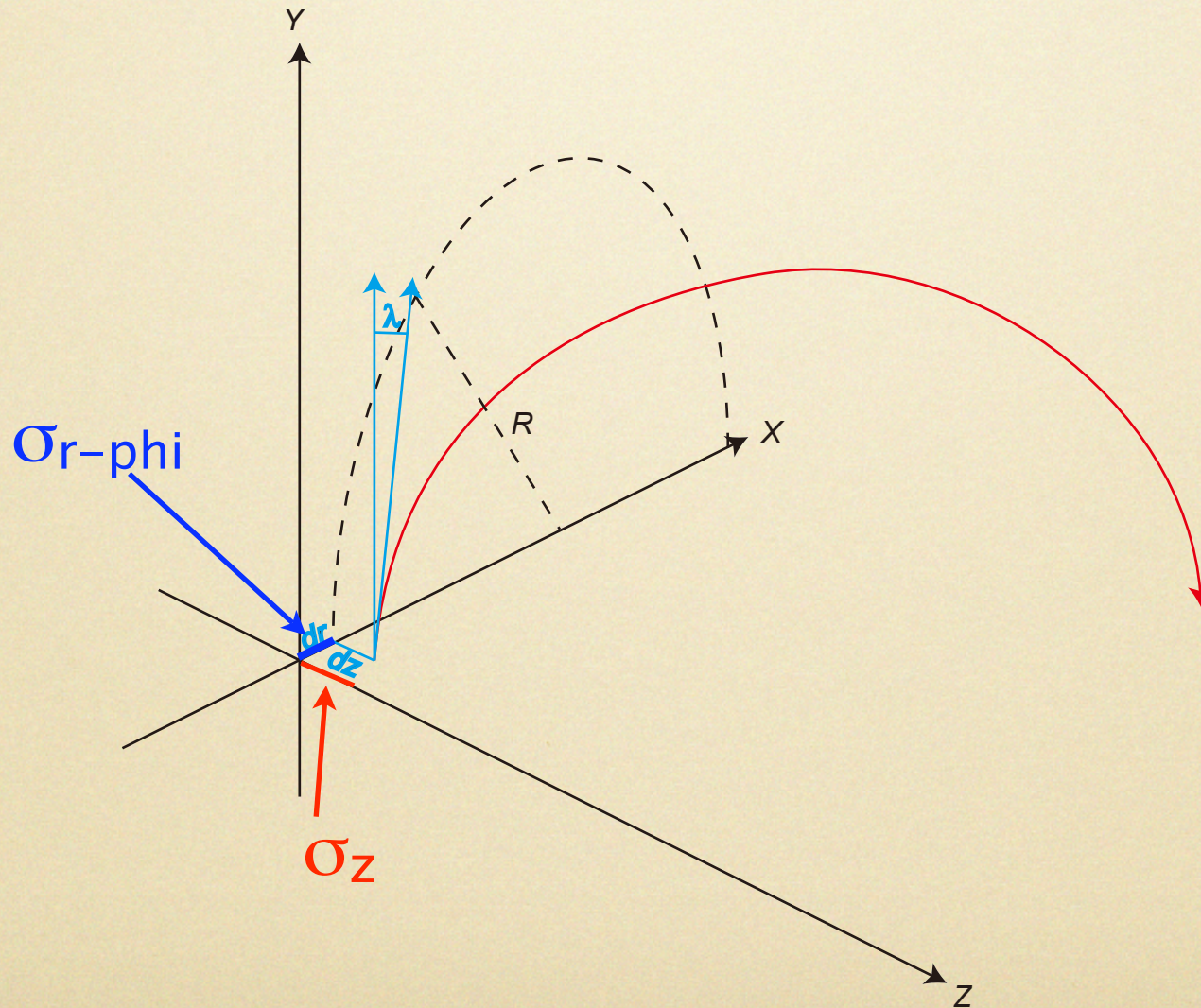
CCD Cross Section

Geometry for Simulation Study

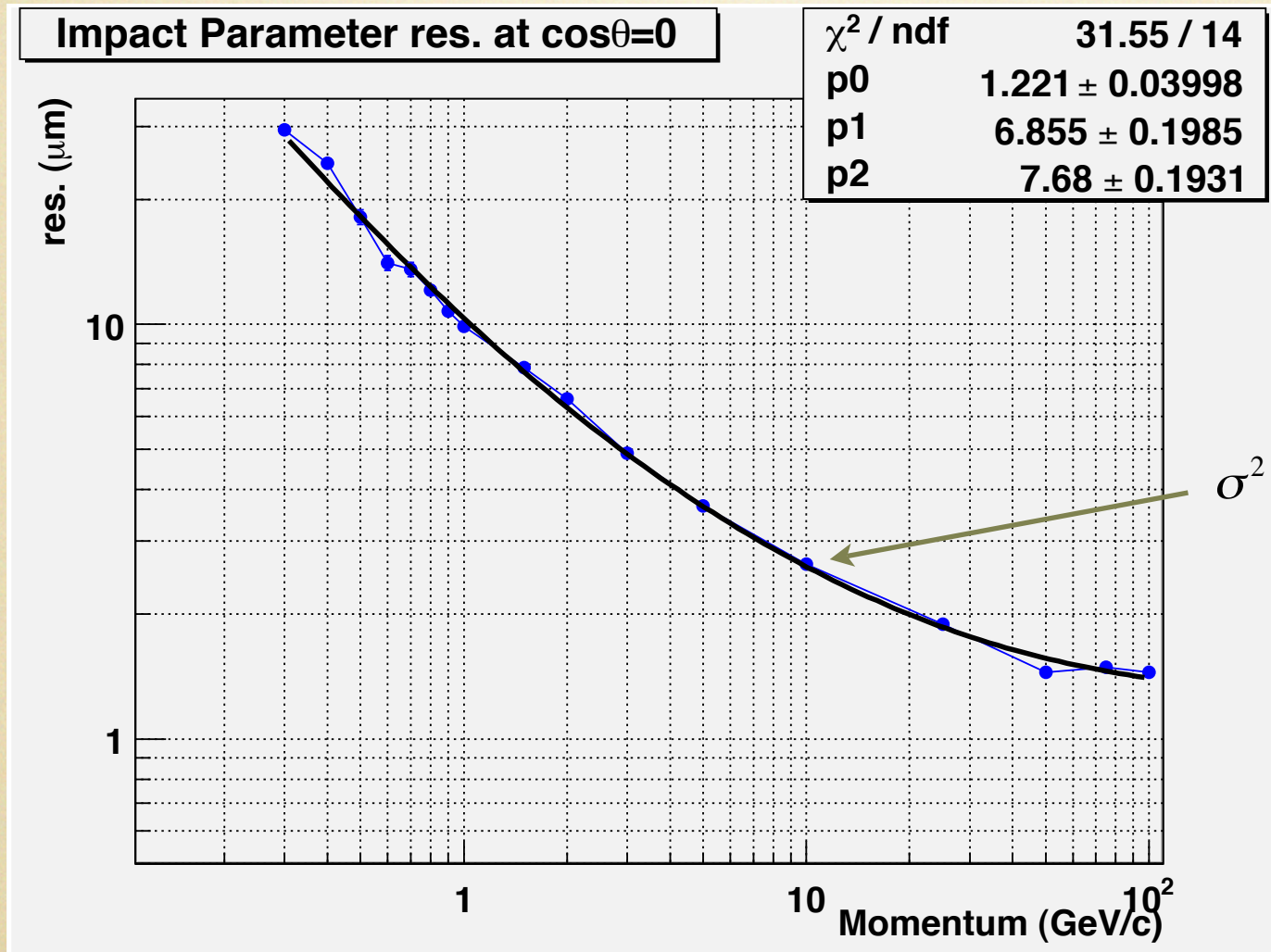


- Tube shape used as each layer
- Layer thickness : $80\mu\text{m}$
- $50\mu\text{m}$ for CCD , $30\mu\text{m}$ for Support Material, Air used for gaps
- 2 mm separation for each doublet
- 3 configurations are studied
- Doublet 1 : $R= 20$ mm
- Doublet 2 : $R= 32$ mm
- Doublet 3 : $R= 48$ mm
- Hit position resolution: $2\mu\text{m}$
- Beam Pipe : Be, $t=250\mu\text{m}$, $R=18\text{mm}$

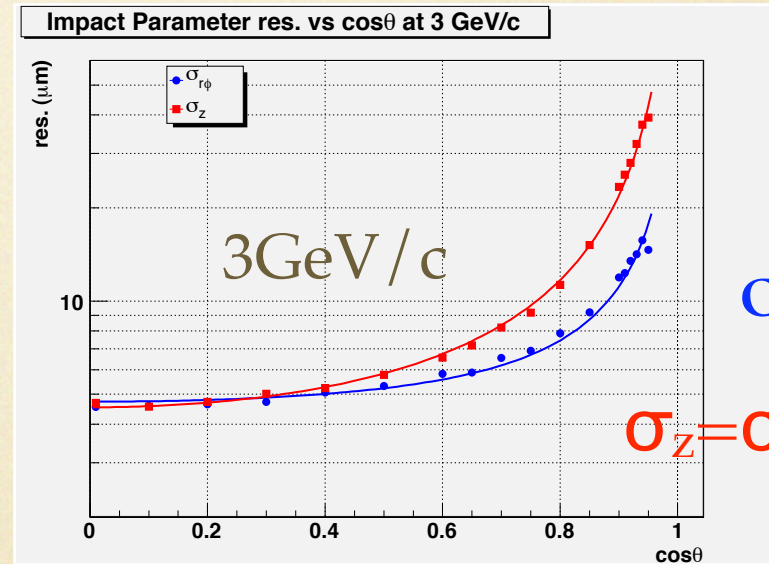
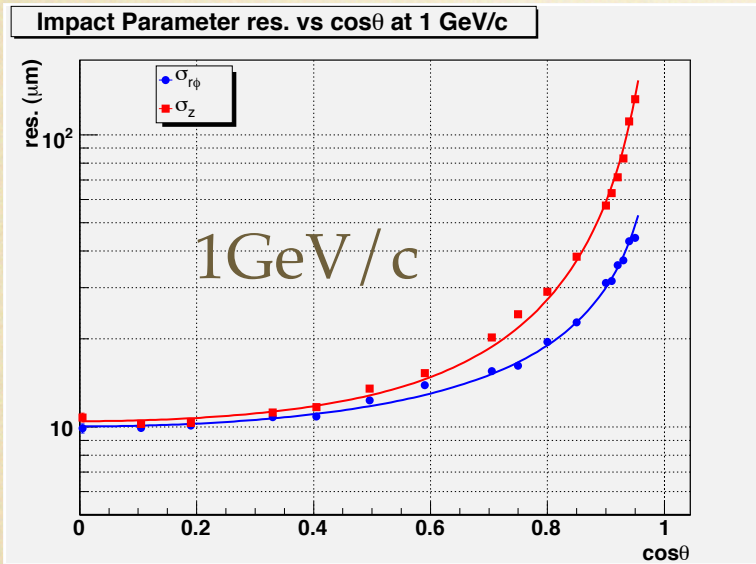
Impact Parameter Study and Helix Parameter



Impact Parameter Resolution $\sigma_{r-\phi}$ Momentum Dependence

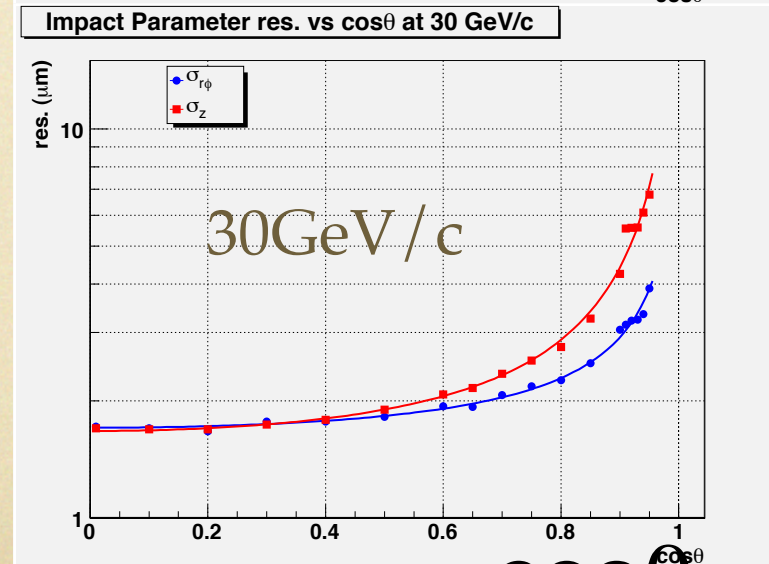
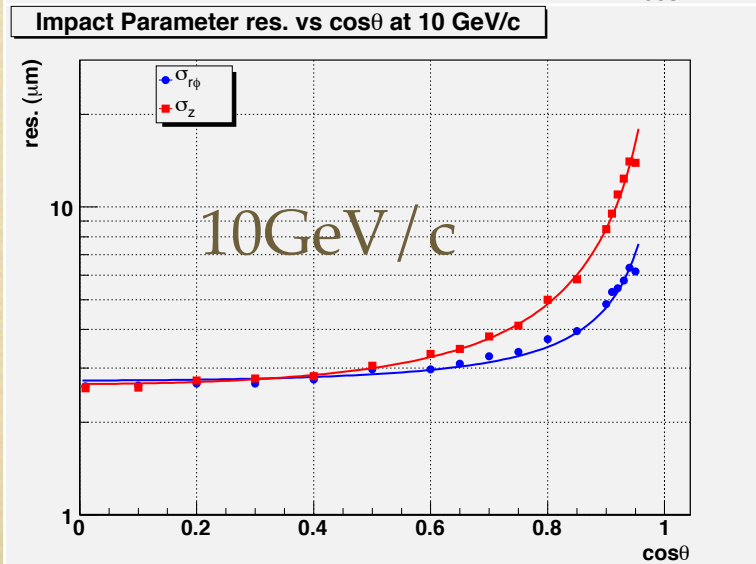


Impact Parameter Resolution $\cos\theta$ dependence at 1,3,10 and 30 GeV/c



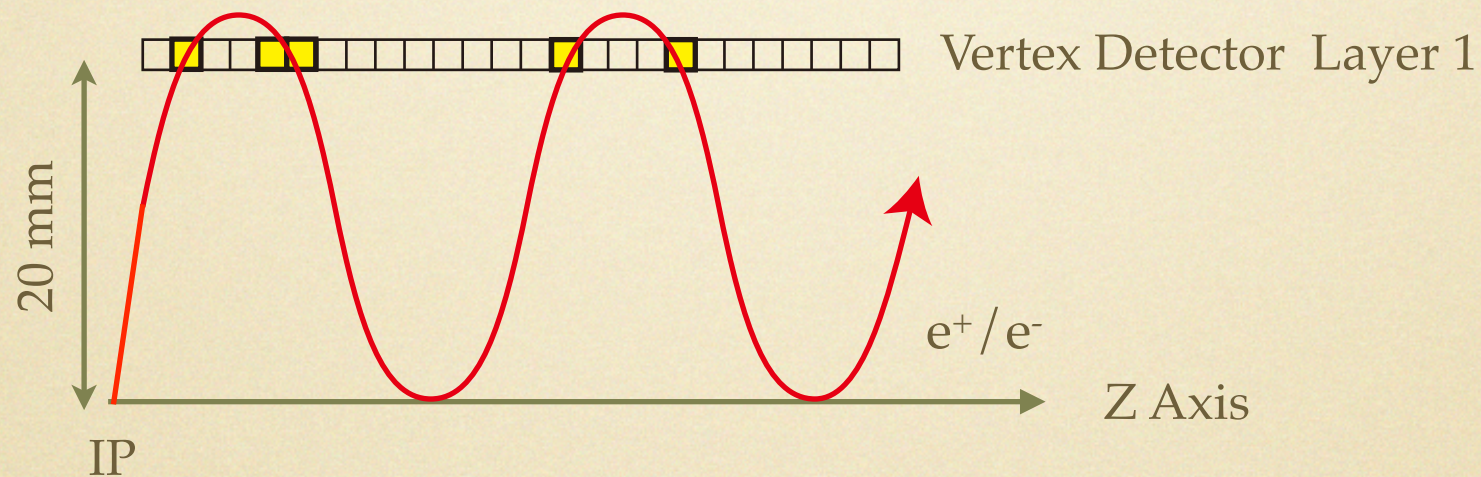
$\sigma_{r\phi}$

$$\sigma_z = \sigma_{r-z} / \sin\theta$$



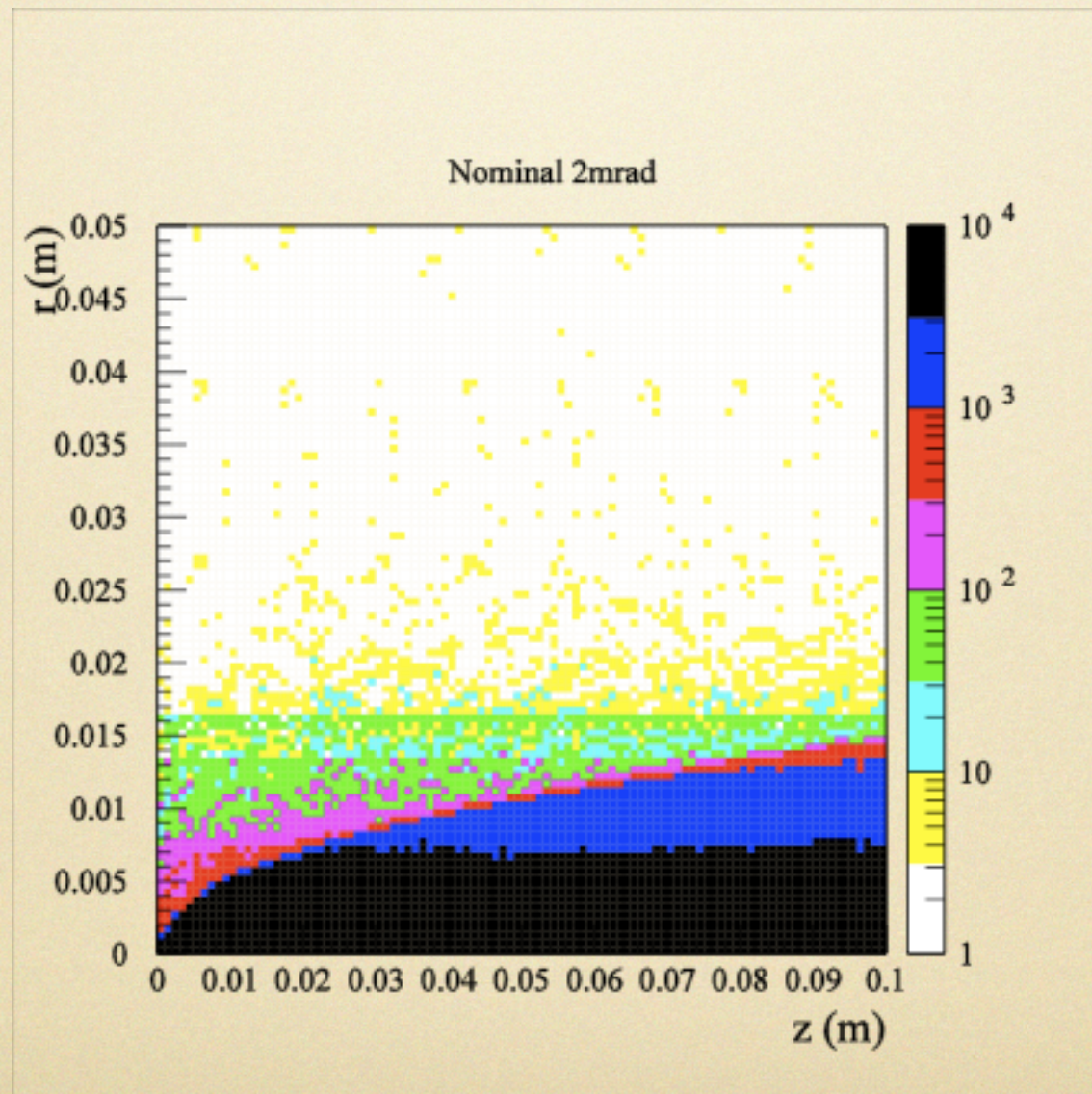
cos θ

Pair Background Trajectory



- Pair Background(e^+/e^-) have low- P_t
- Their Radii are small
- They hit the vertex detector many times

Distribution of Pair Background in Vertex Region

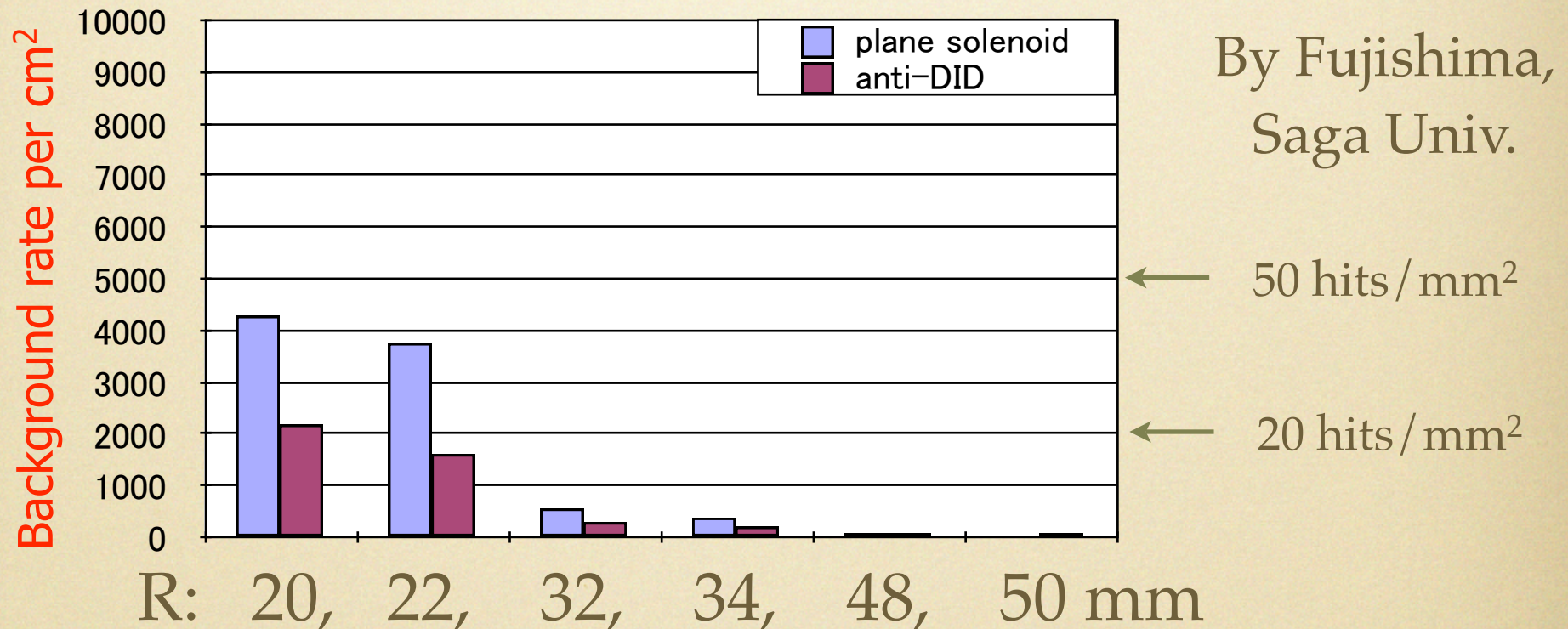


$B=3T$

By Sugimoto

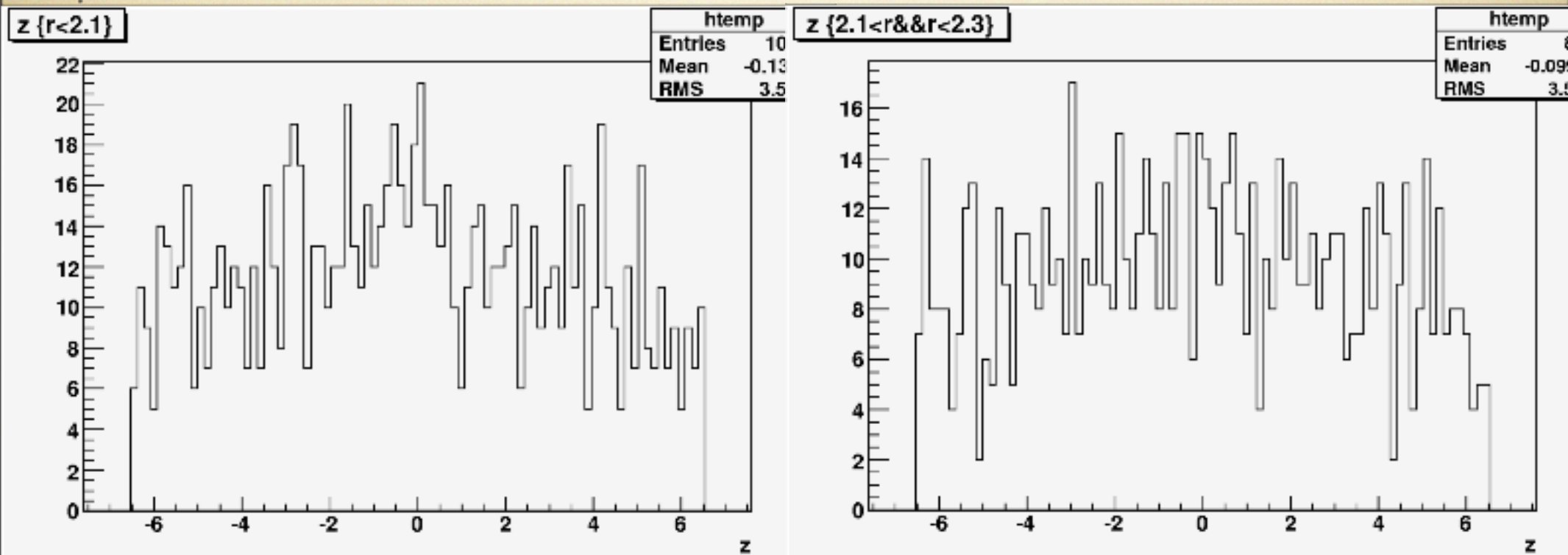
Background rate

Plain vs. anti-DID in VTX



- CAIN/Jupiter/Geant4 results
- Beam Parameter: nominal 500GeV, 14mrad
- Background rate is reduced to 1/2 with ANTI-DID Field

z distribution of VTX hits



Layer 1

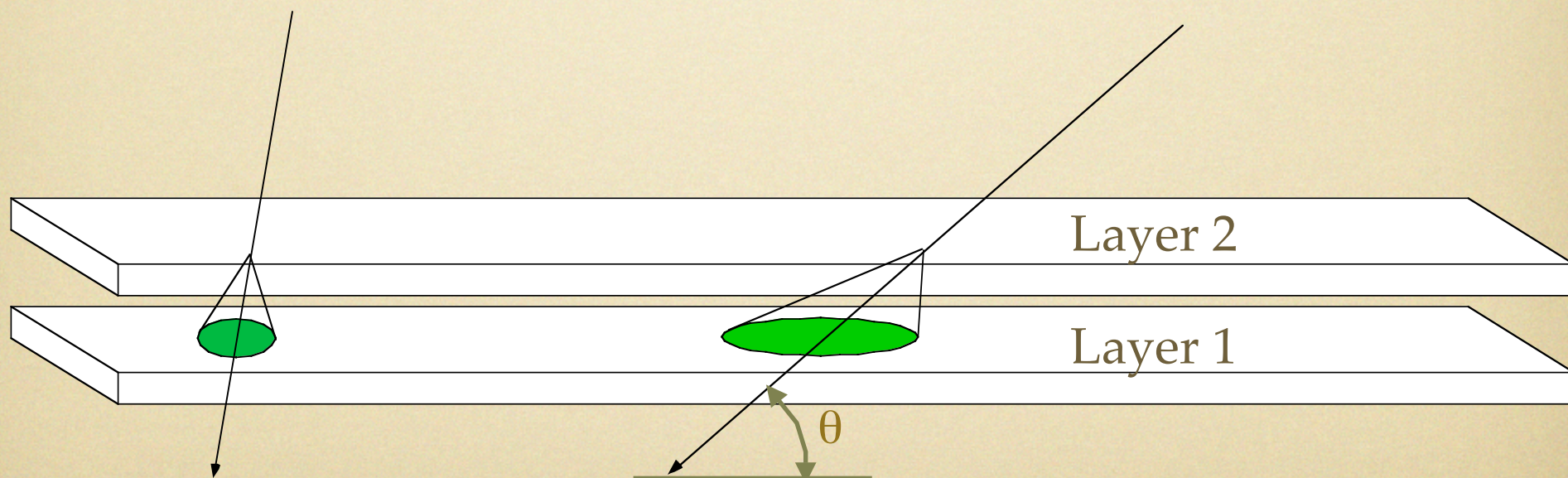
Layer 2

Small Z dependence

By Fujishima

Track Finding

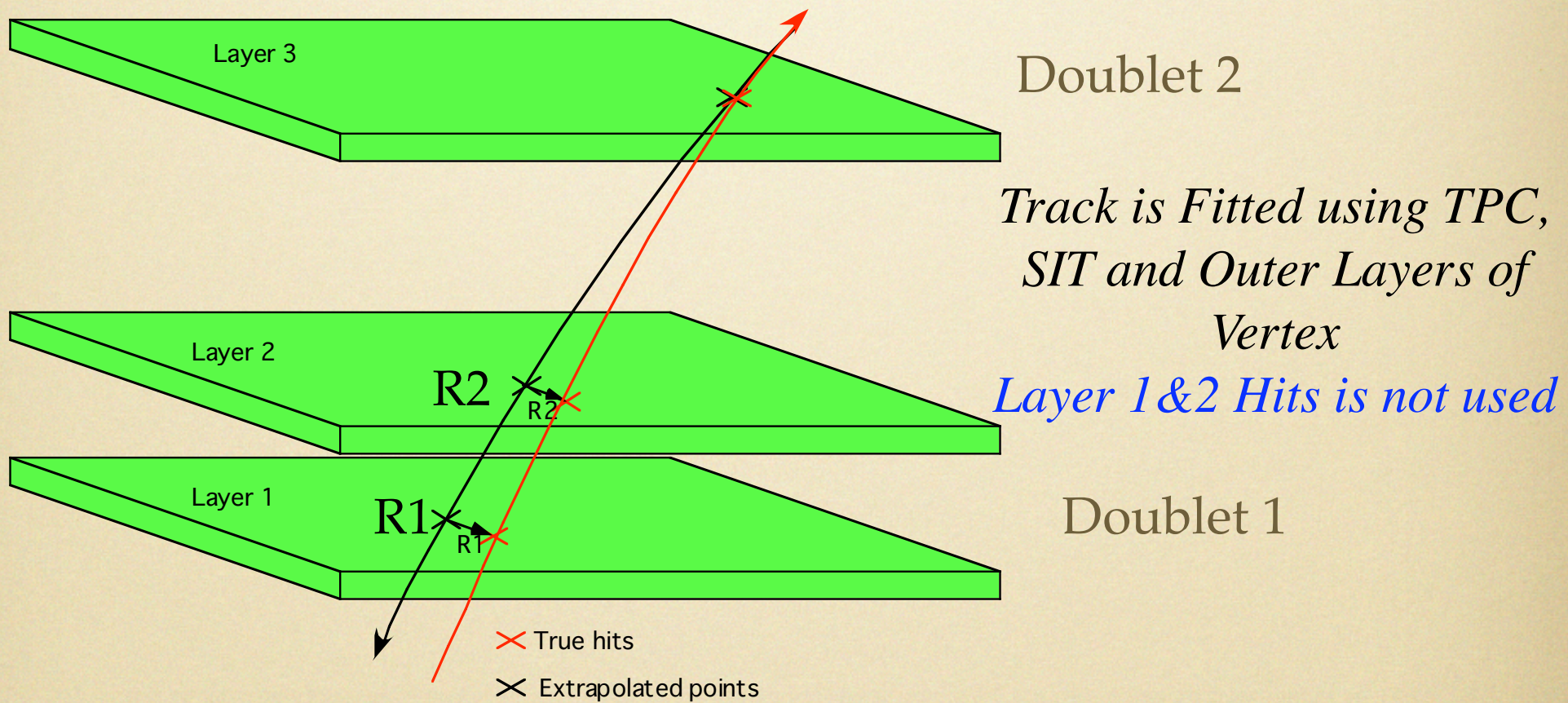
- Track Finder is under development in SimTools!
- Efficiency depends on hit probability in track finding window.
- Track finding window(area) from impact parameter resolution at the layer
- Area depends on polar angle of track as $1 / \sin^4\theta$



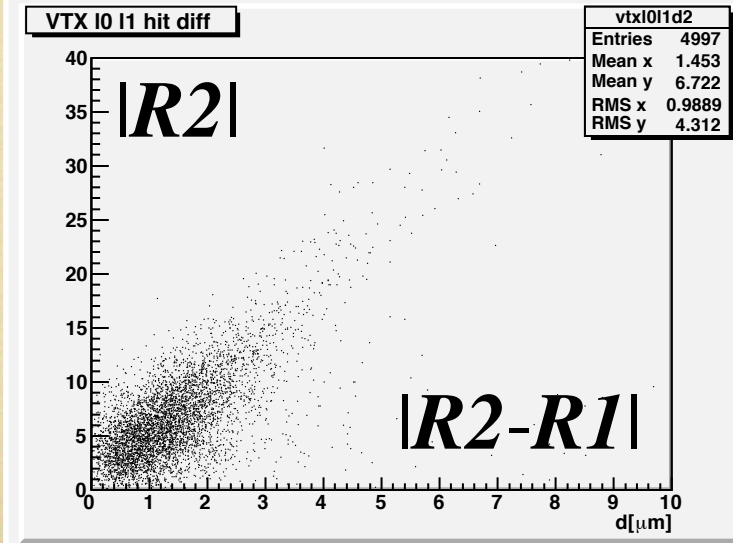
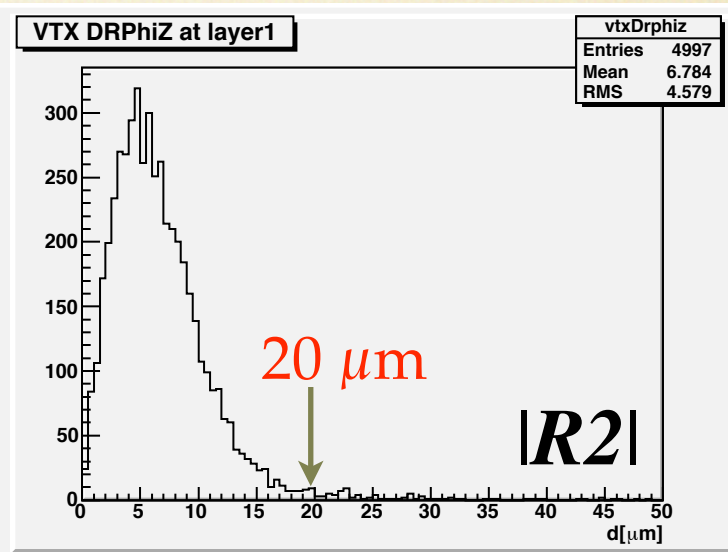
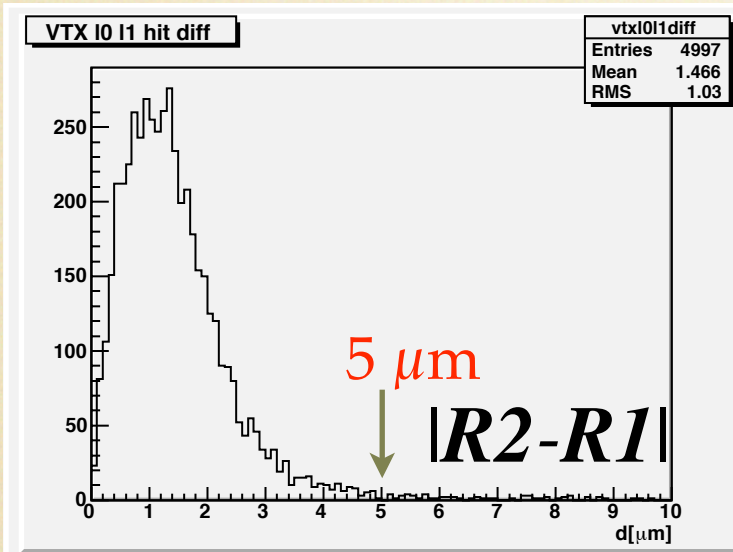
Effect of Background on Track Finding

- Estimate track-hit matching efficiency using Toy MC
- Generate a true hit around a track with distribution functions obtained by Full MC
- Generate Background hits randomly around the track ; 50, 100 and 200 hits / mm²
- Accept the true hit closer to the track than background hits
- Ignoring finite pixel and cluster sizes

Track-Hit Matching Efficiency

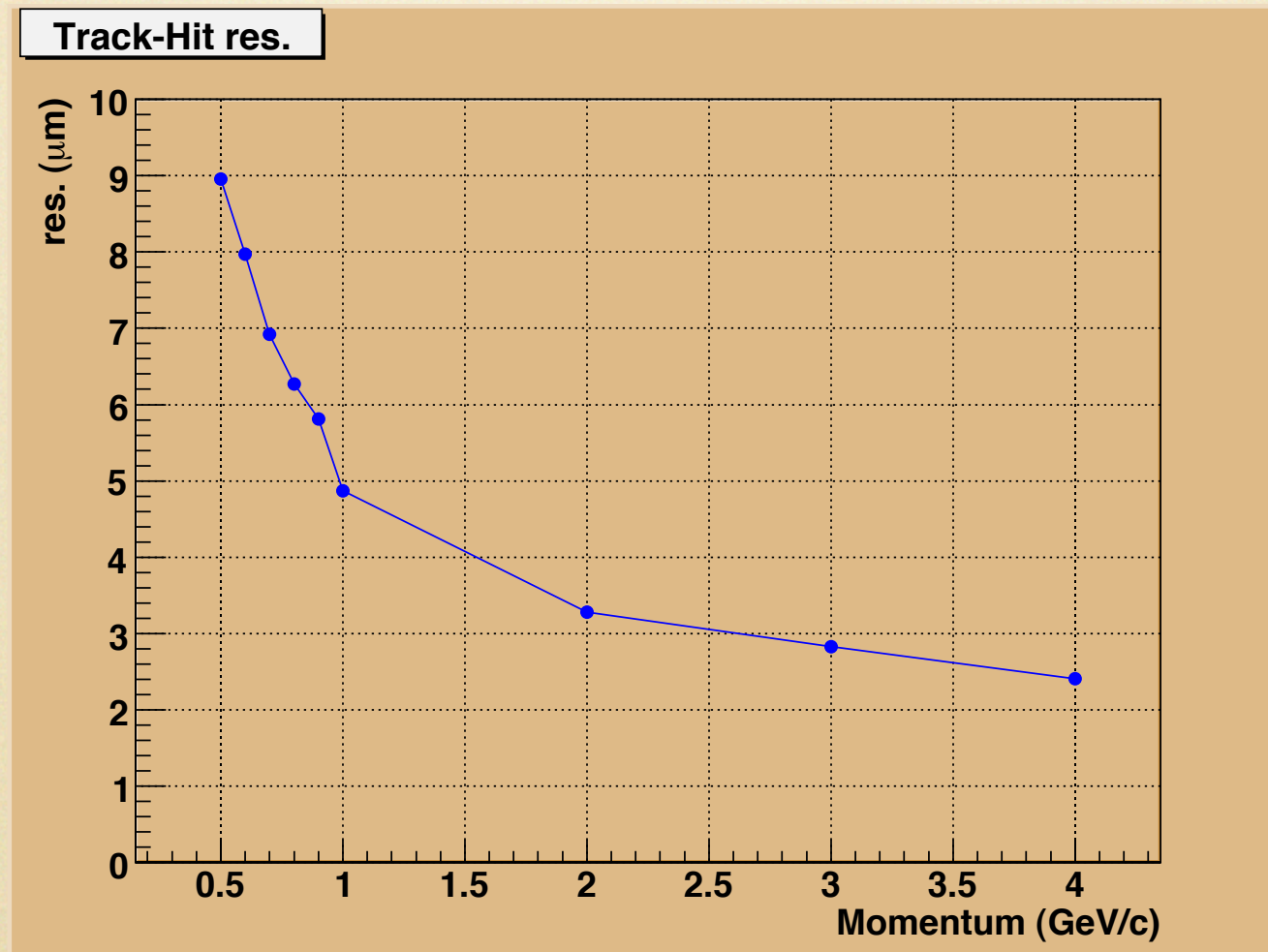


Track-Hit differences distributions



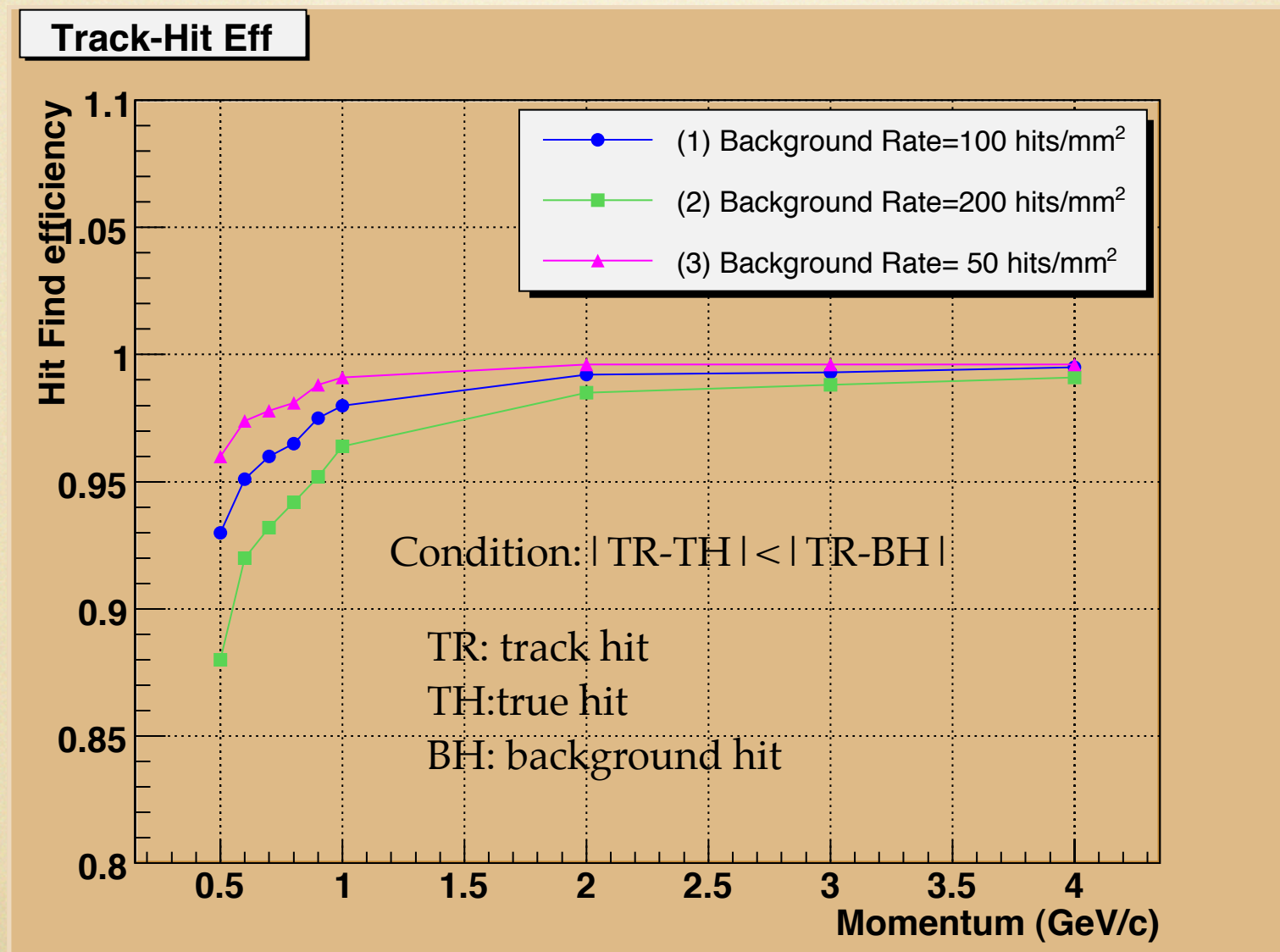
Muon
1 GeV/c
COS θ =0.05

$|R2|$ resolution v.s. Momentum



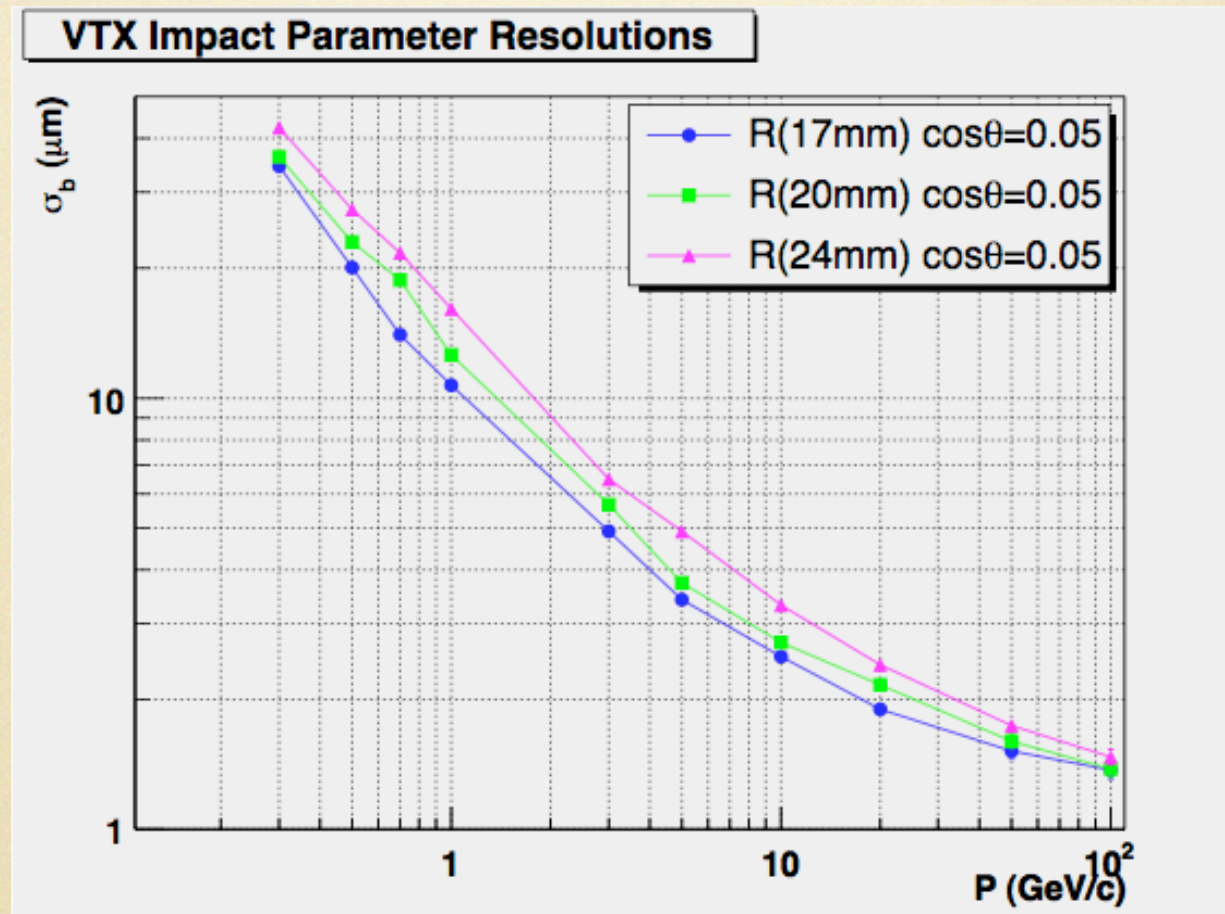
$\sim 1/3$ of Impact Parameter Resolution at IP

Efficiencies for different hit rates



- FPCCD based Vertex Detector can work under hit rate up to $50 / \text{mm}^2$
- The reasons:
 - Good Outer Tracking detector - SIT and TPC
 - Vertex has 6 Layer - 4 layer can use for extrapolate to inner most layer
 - Vertex detector layers are very thin
 - Small pixel size which matches to the resolution

Impact Parameter Resolution R dependence (OLD Geometry)

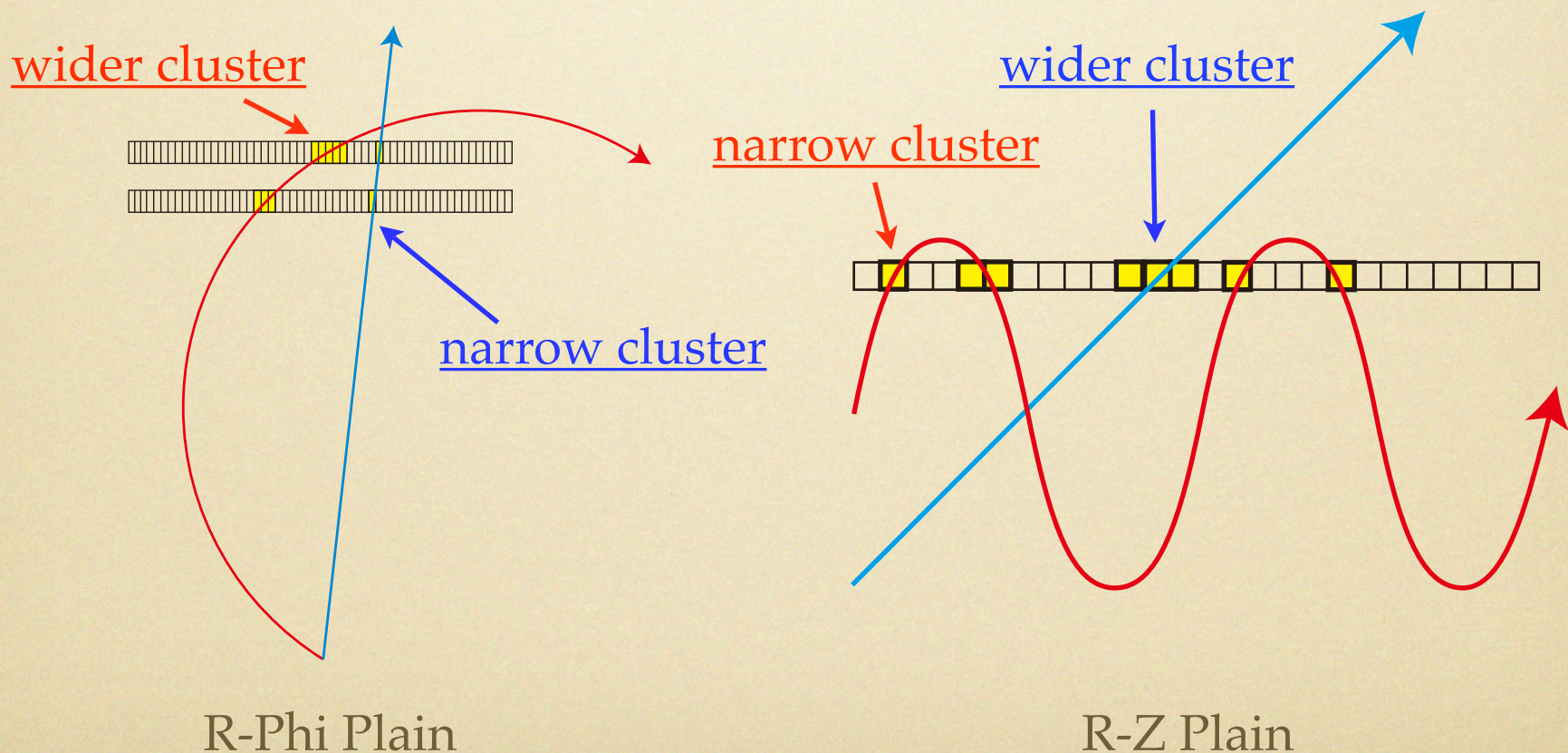


- Impact Parameter Resolution(R-phi plane) v.s. Momentum
- μ^- at $\cos(\theta)=0.05$
- Impact Parameter Resolution increases as radius increases

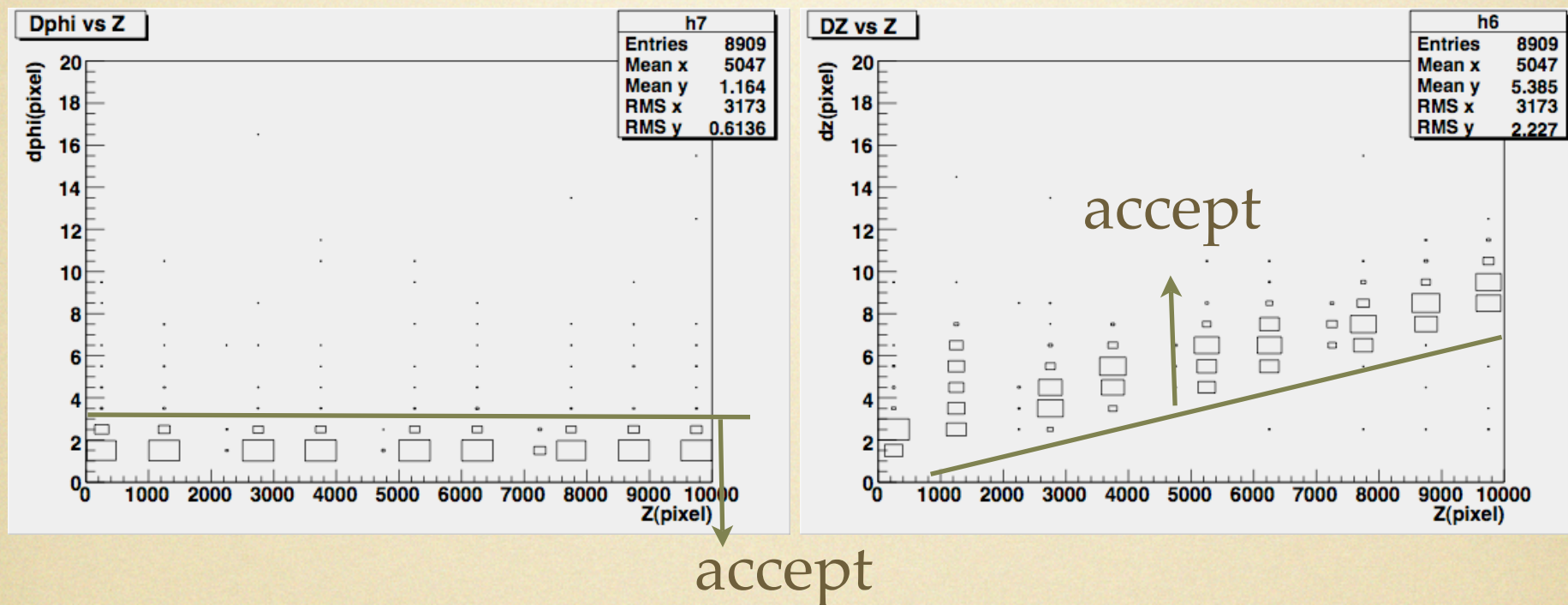
Cluster Shapes for Low-Pt and High-Pt tracks

RED: Low-Pt Track (Pair Background)

BLUE: High-Pt Track

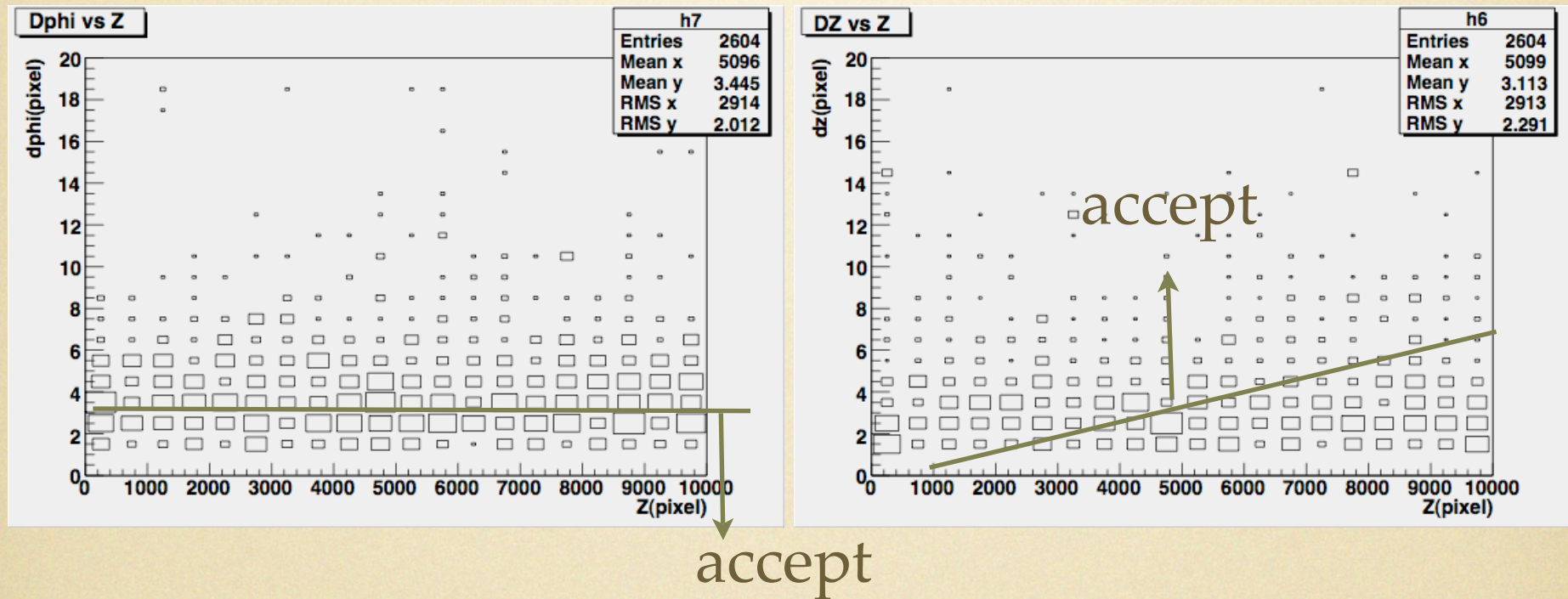


Distributions of Cluster Width v.s. Z for Muon Tracks



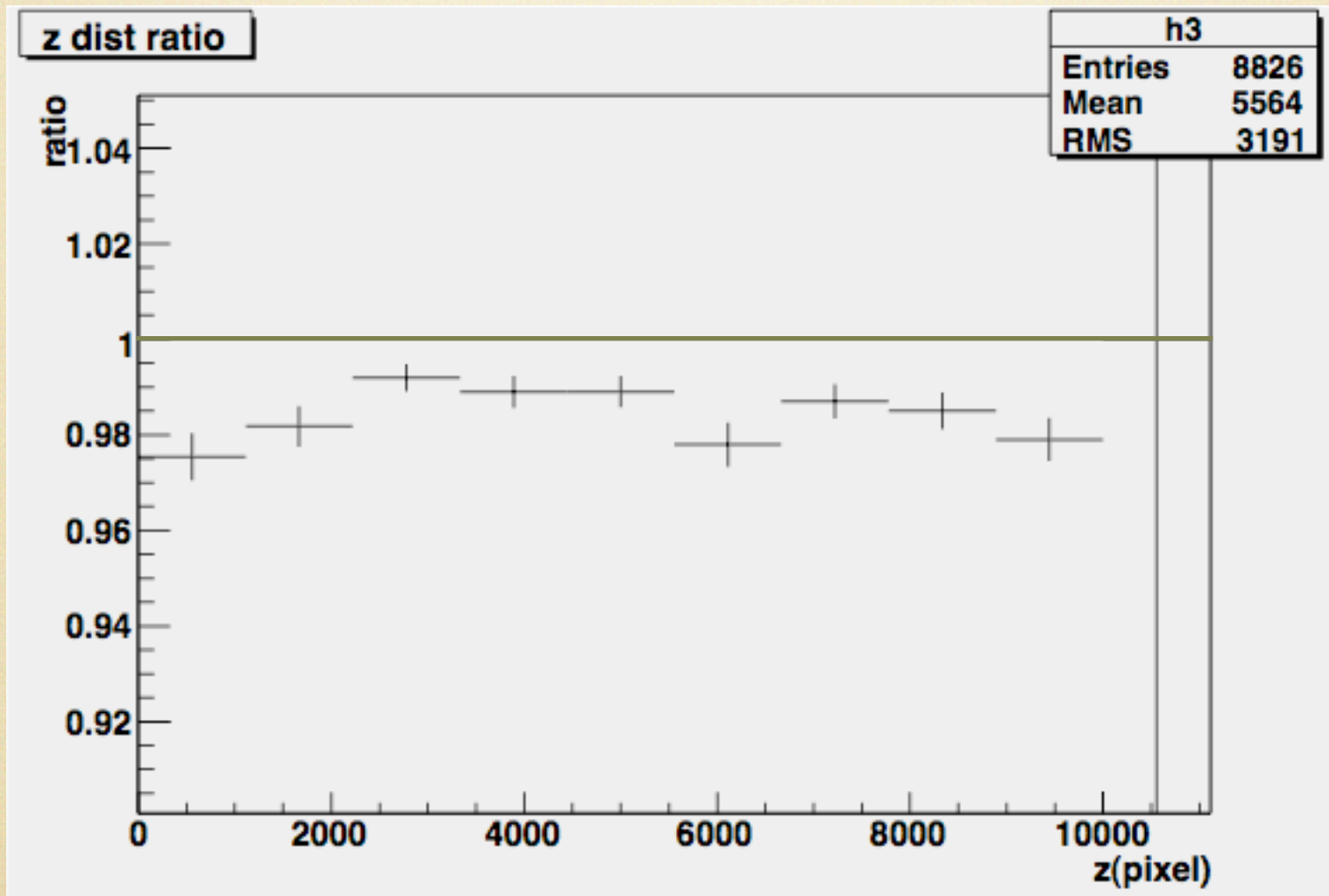
- 1 GeV/c μ^-
- Left: R-Phi, Right: R-Z
- Clear Z dependence of Cluster Width in R-Z

Distributions of Cluster width v.s. Z for Pair Background



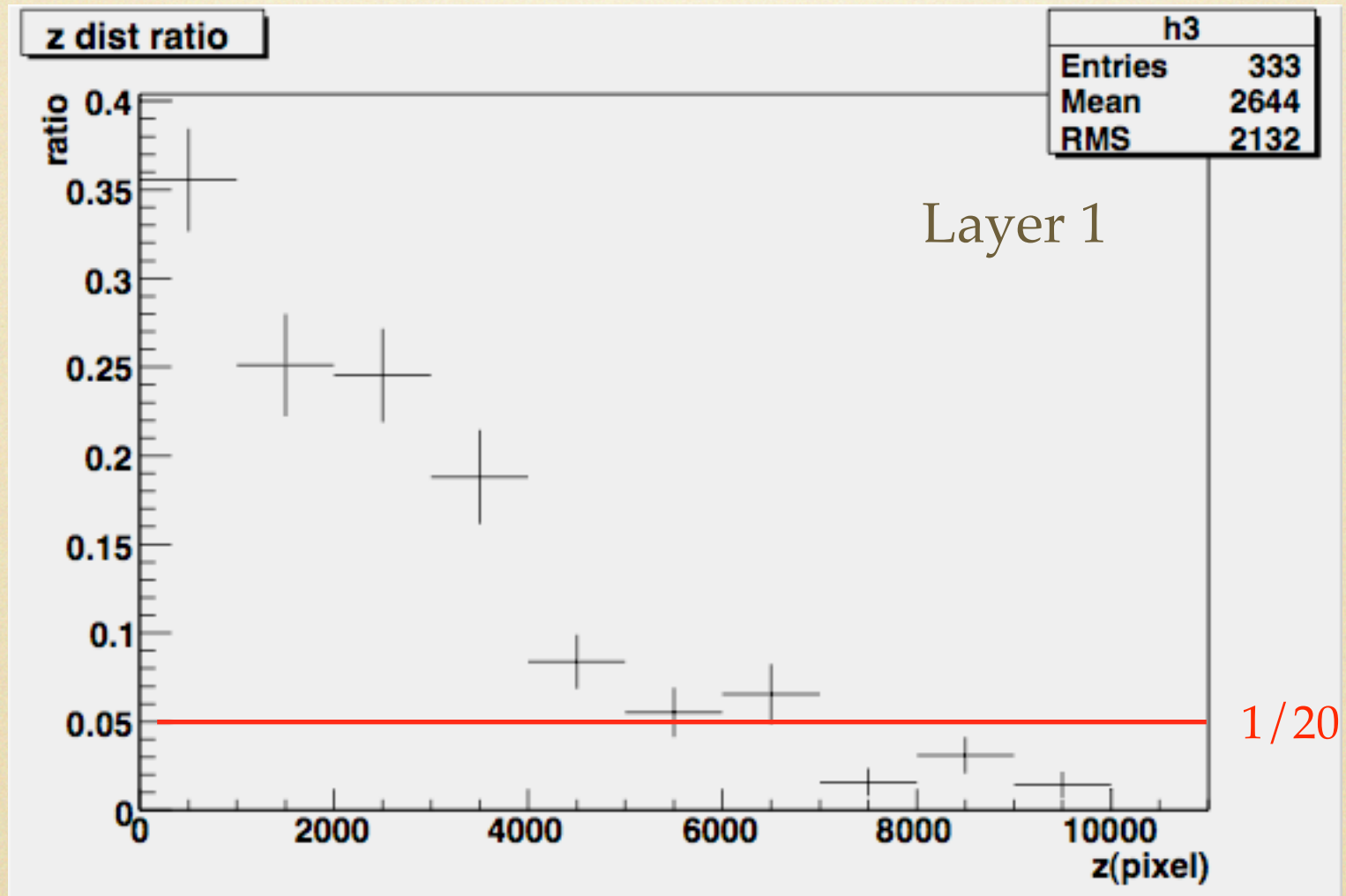
- Pair background
- Left: R-Phi, Right: R-Z
- No Z dependence in both R-Phi and R-Z

Efficiency for Muon track



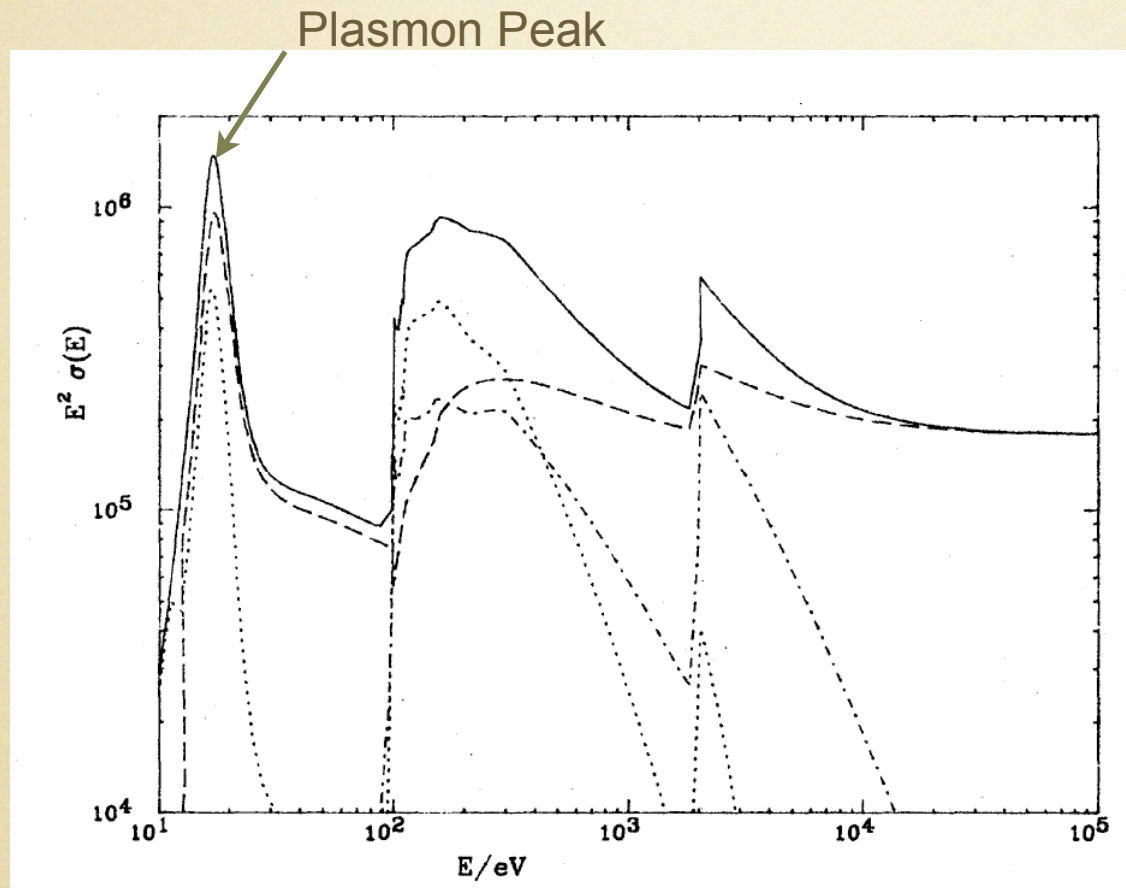
- 1GeV/c μ^-

Efficiency for Pair Background



- Rejection factor is $1/2 \sim 1/20$ depend on Z

Energy Deposit in Thin material



- Effect of statistical fluctuation of collision
- Effect of Plasmon Excitation

differential collision cross section in Silicon

H. Bichsel, Rev. Mod. Phys. 60, p663

Plasmon Spectrum Measurement by Electron Spectrometer

J. Perez, et al, PR A16, p1061

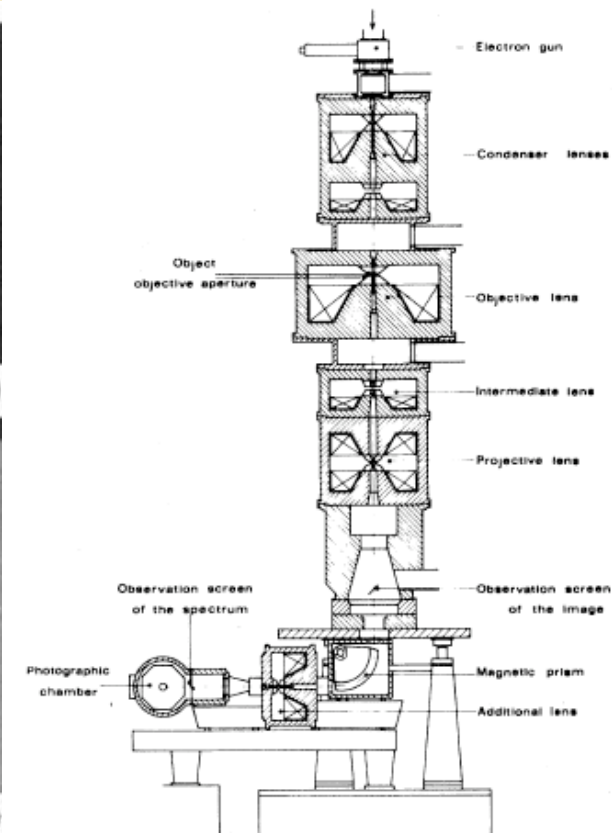
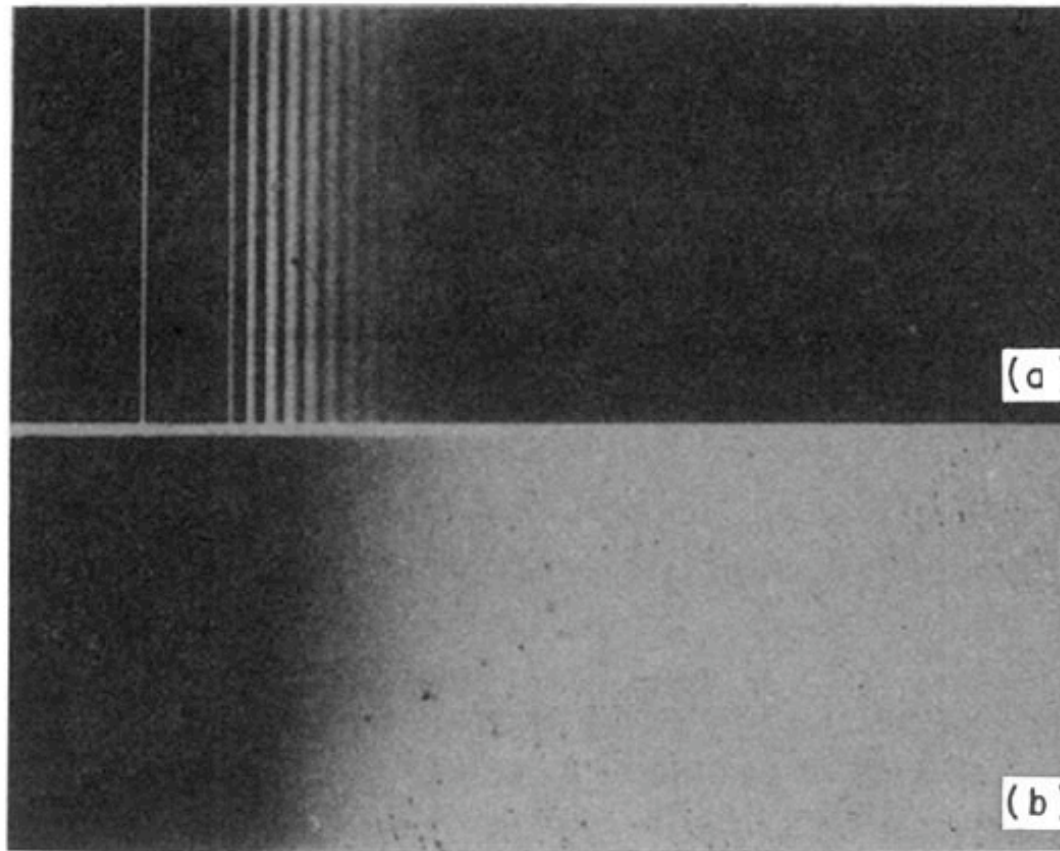
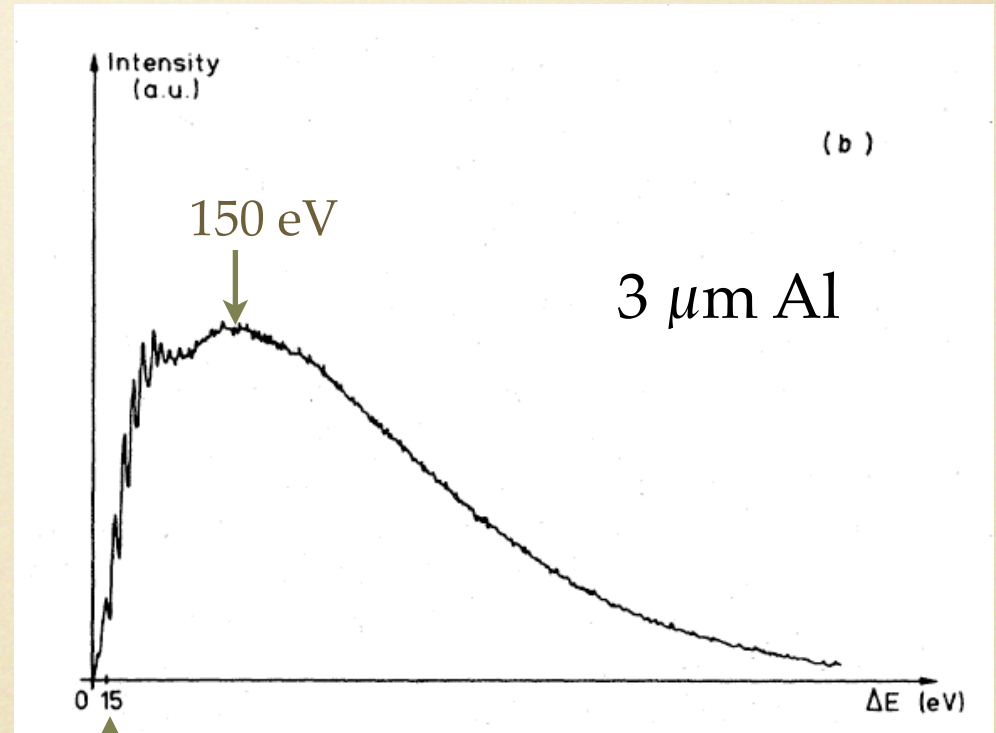
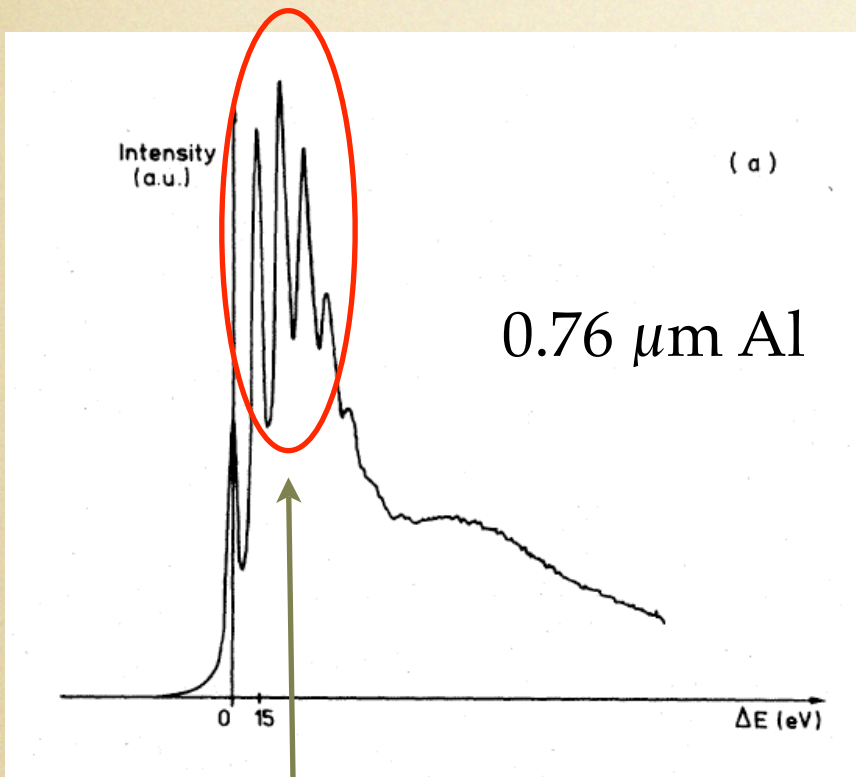


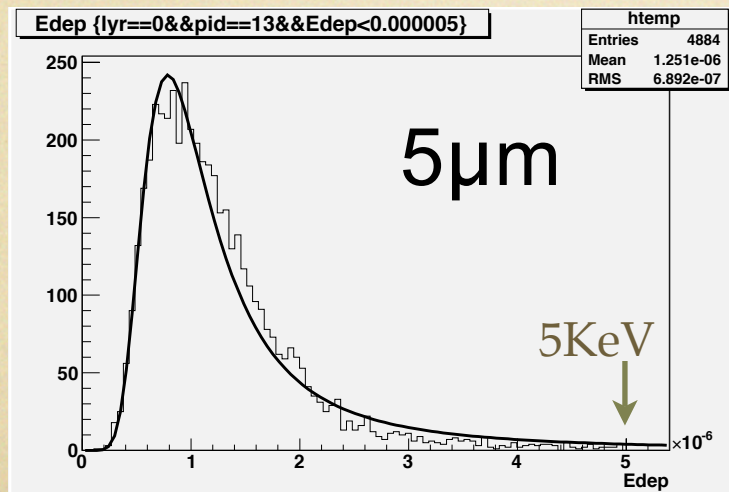
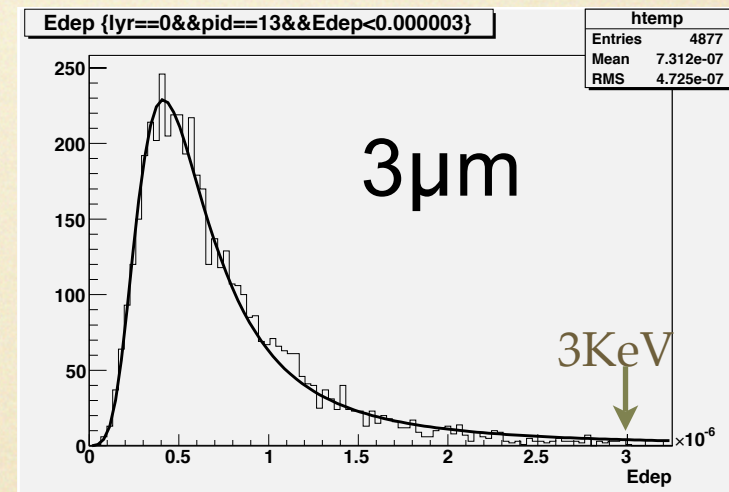
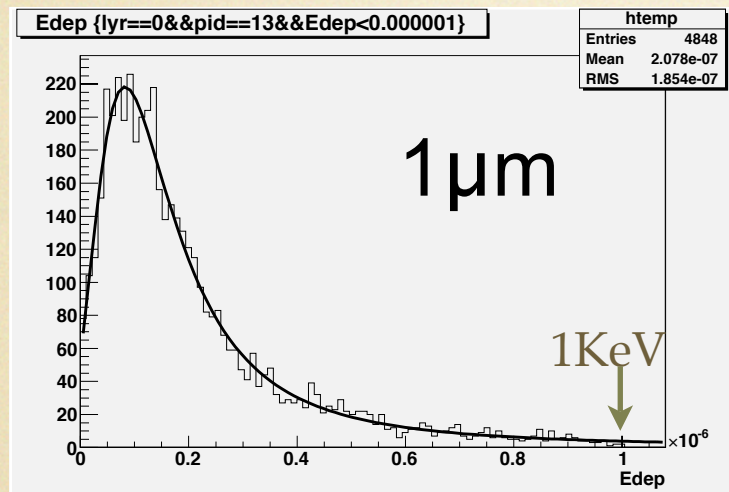
FIG. 1. Cross section of the high-voltage electron analyzer.

Electron Energy Loss 0.76 and 3 μm Al, $T=1.0$ MeV



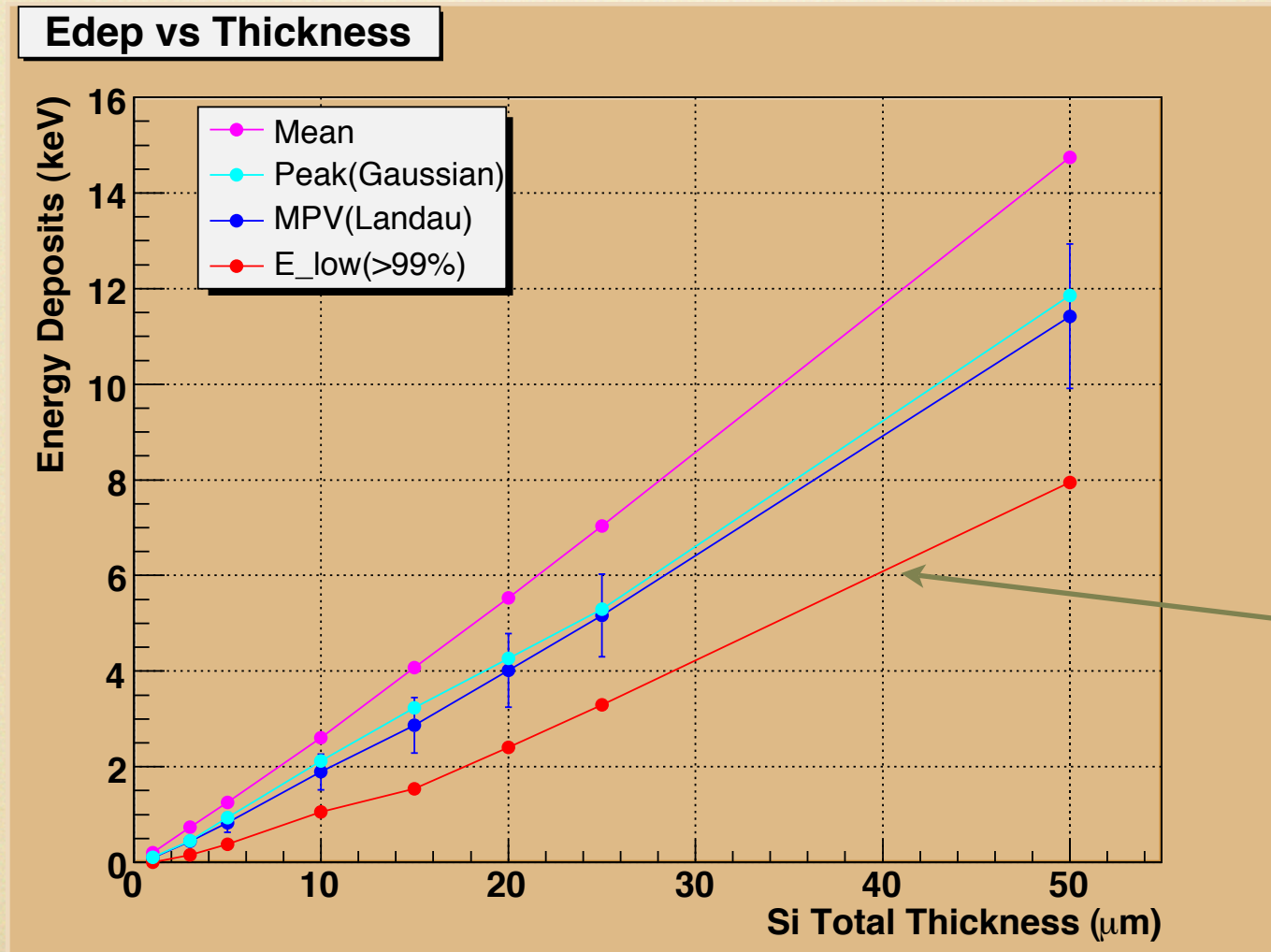
- Plasmon Peaks:
15eV separation

Energy deposit of $t=1,3,5\mu\text{m}$ Si Geant4 Simulation



1 GeV/c Muon
No Plasmon Peaks seen

MPV and $E_{low}(>99\%)$



$E_{low}(>99\%)$

Summary

- Current design of FPCCD base Vertex detector has good Impact Parameter Resolution
- Good tracking efficiency can be expected under high background rate (100 hits/mm²) for higher momentum region, and up to 50 hits/mm² for lower momentum region
- Good Pair Background rejection can be expected by Cluster shape (rejection factor = 1/2~1/20)
- Need more study for Energy deposit in thin Si
- Need to study b,c and tau tagging in physics events(Z, ZH, etc)